



UK1398

Power MOSFET

N-CHANNEL MOSFET FOR HIGH SPEED SWITCHING

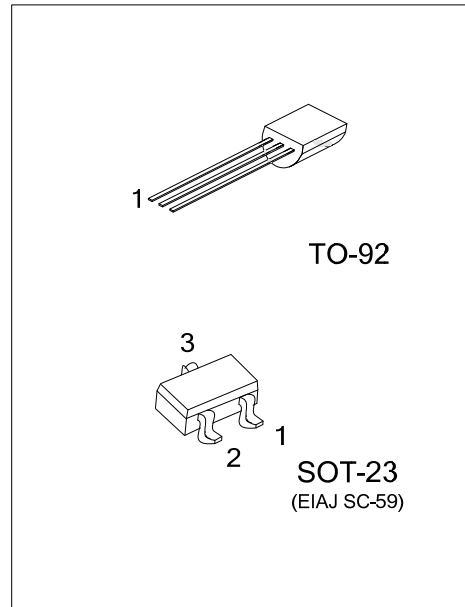
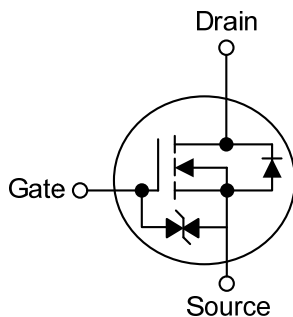
DESCRIPTION

The UTC **UK1398** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} < 40\Omega$ @ $V_{GS}=2.5V, I_D=10mA$
- * $R_{DS(ON)} < 20\Omega$ @ $V_{GS}=4.0V, I_D=10mA$
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

SYMBOL

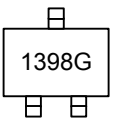
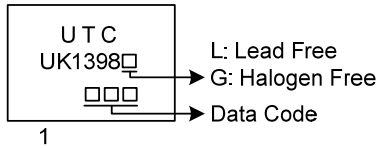


ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	UK1398G-AE3-R	SOT-23	S	G	D	Tape Reel
UK1398L-T92-B	UK1398G-T92-B	TO-92	S	D	G	Tape Box
UK1398L-T92-K	UK1398G-T92-K	TO-92	S	D	G	Bulk

<p>UK1398G-AE3-R</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AE3: SOT-23, T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING

SOT-23	TO-92
	

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	± 7.0	V
Continuous Drain Current	DC	± 100	mA
	Pulse(Note 2)	± 200	mA
Power Dissipation	SOT-23	200	mW
	TO-92	625	
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

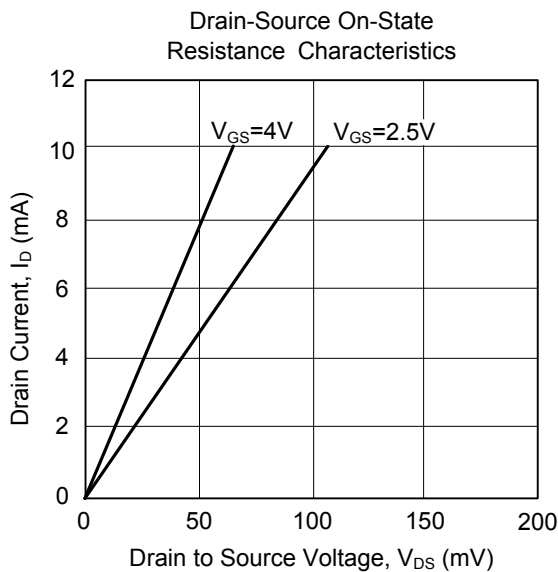
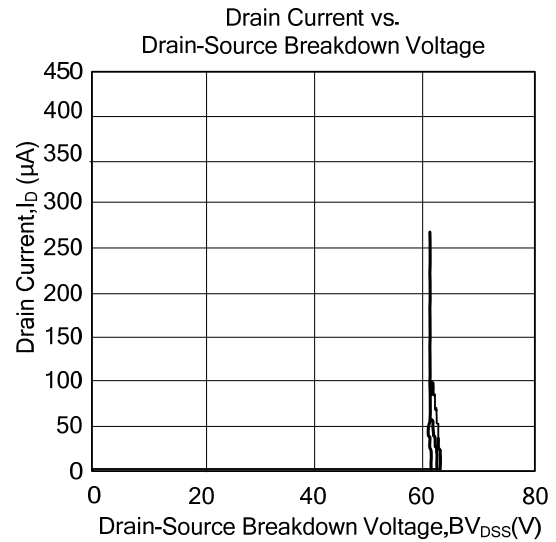
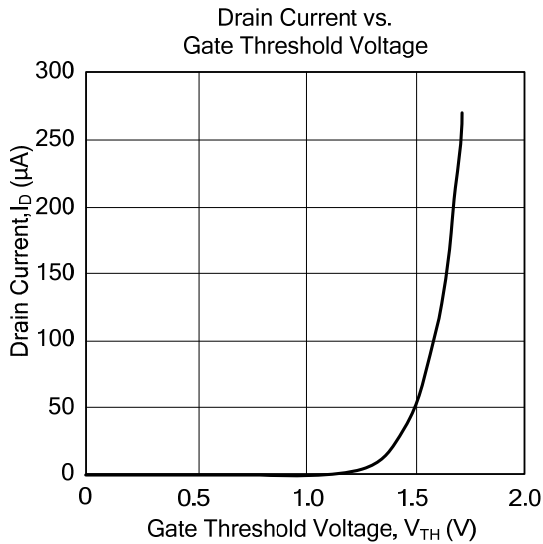
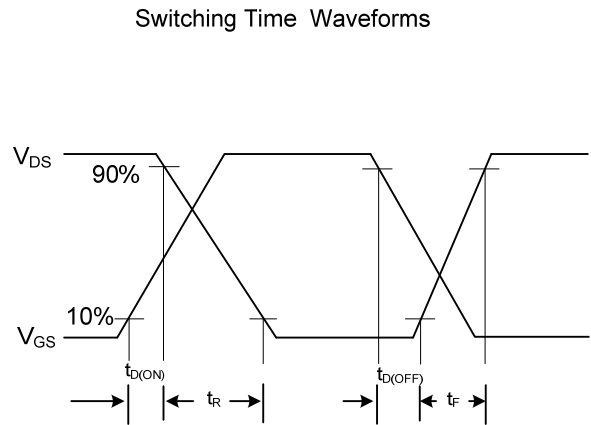
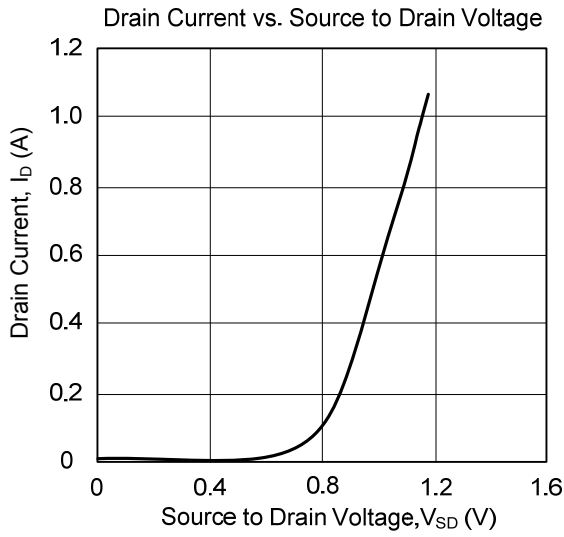
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width $\leq 10\text{ms}$, Duty cycle $\leq 50\%$

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	50			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=50\text{V}, V_{GS}=0\text{V}$			10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 7.0\text{V}, V_{DS}=0\text{V}$			± 5.0	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0		3.0	V
	$V_{GS(OFF)}$	$V_{DS}=3.0\text{V}, I_D=1.0\mu\text{A}$	0.6	1.2	1.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=10\text{mA}$		22	40	Ω
		$V_{GS}=4.0\text{V}, I_D=10\text{mA}$		14	20	Ω
Forward Transconductance	g_{FS}	$V_{DS}=3.0\text{V}, I_D=10\text{mA}$	20	38		mS
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=3.0\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		8		pF
Output Capacitance	C_{OSS}			7		pF
Reverse Transfer Capacitance	C_{RSS}			3		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=3.0\text{V}, I_D=20\text{mA},$ $V_{GS(ON)}=3.0\text{V}, R_G=10\Omega,$ $R_L=150\Omega$		15		ns
Turn-ON Rise Time	t_R			100		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			30		ns
Turn-OFF Fall-Time	t_F			35		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}, V_{GS}=0\text{V}$			1.3	V

TYPICAL CHARACTERISTICS



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